

STARPOWER

SEMICONDUCTOR

IGBT

GD100FFL170C6S

1700V/100A 6 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

Features

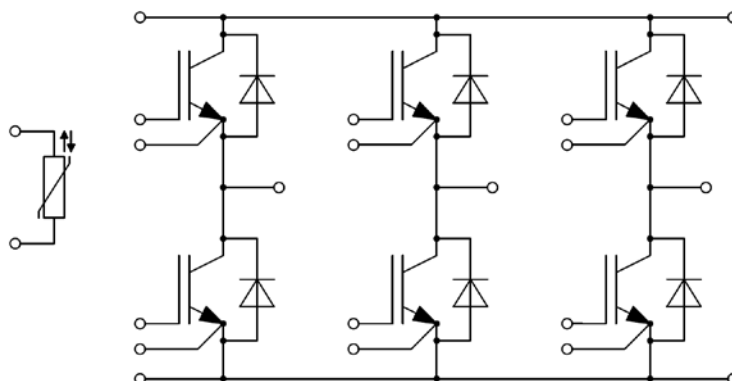
- Low $V_{CE(sat)}$ SPT+ IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1700	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	157	A
	@ $T_C=100^{\circ}\text{C}$	100	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	200	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	714	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1700	V
I_F	Diode Continuous Forward Current	100	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.40	2.85	V	
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		2.80			
		$I_C=100\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.90			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=4.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.4	6.2	7.4	V	
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
R_{Gint}	Internal Gate Resistance			7.7		Ω	
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		6.75		nF	
C_{res}	Reverse Transfer Capacitance			0.23		nF	
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.77		μC	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=100\text{A}, R_G=4.1\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		206		ns	
t_r	Rise Time			71		ns	
$t_{d(off)}$	Turn-Off Delay Time			232		ns	
t_f	Fall Time			455		ns	
E_{on}	Turn-On Switching Loss			23.8		mJ	
E_{off}	Turn-Off Switching Loss			15.4		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=900\text{V}, I_C=100\text{A}, R_G=4.1\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		219		ns
t_r	Rise Time				81		ns
$t_{d(off)}$	Turn-Off Delay Time			267		ns	
t_f	Fall Time			732		ns	
E_{on}	Turn-On Switching Loss			32.5		mJ	
E_{off}	Turn-Off Switching Loss			24.3		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=900\text{V}, I_C=100\text{A}, R_G=4.1\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			219		ns
t_r	Rise Time				83		ns
$t_{d(off)}$	Turn-Off Delay Time			270		ns	
t_f	Fall Time			797		ns	
E_{on}	Turn-On Switching Loss			34.2		mJ	
E_{off}	Turn-Off Switching Loss			26.6		mJ	
I_{SC}	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=1000\text{V}, V_{CEM} \leq 1700\text{V}$		310		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.80	2.25	V
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		1.95		
		$I_F=100\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		1.90		
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=100\text{A},$ $-di/dt=1350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		23.6		μC
I_{RM}	Peak Reverse Recovery Current			91		A
E_{rec}	Reverse Recovery Energy			13.4		mJ
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=100\text{A},$ $-di/dt=1350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		35.7		μC
I_{RM}	Peak Reverse Recovery Current			98		A
E_{rec}	Reverse Recovery Energy			20.8		mJ
Q_r	Recovered Charge	$V_R=900\text{V}, I_F=100\text{A},$ $-di/dt=1350\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		40.0		μC
I_{RM}	Peak Reverse Recovery Current			106		A
E_{rec}	Reverse Recovery Energy			23.5		mJ

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		21		nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		1.80		$\text{m}\Omega$
R_{thJC}	Junction-to-Case (per IGBT)			0.210	K/W
	Junction-to-Case (per Diode)			0.380	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.084		K/W
	Case-to-Heatsink (per Diode)		0.152		
	Case-to-Heatsink (per Module)		0.009		
M	Mounting Screw:M5	3.0		6.0	N.m
G	Weight of Module		300		g

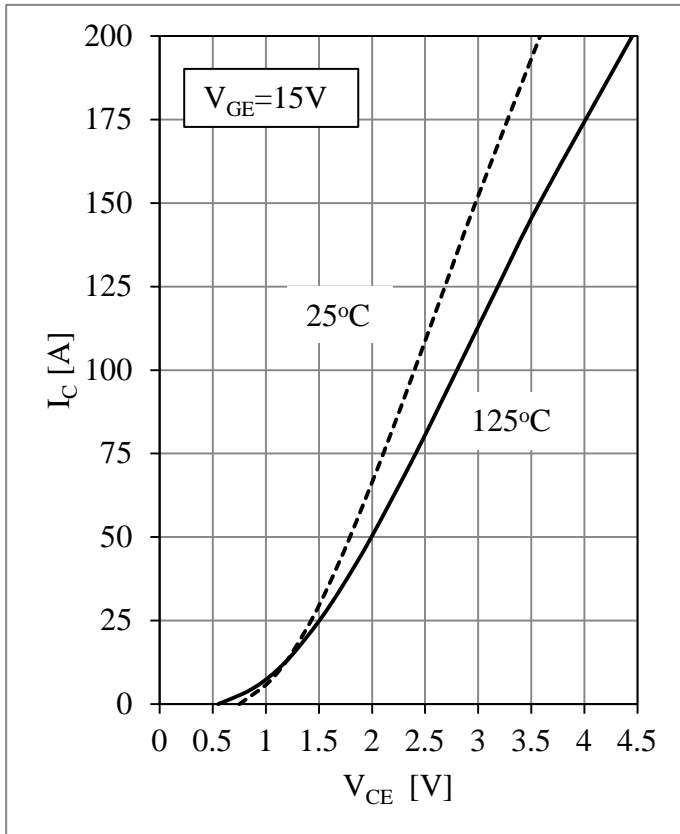


Fig 1. IGBT Output Characteristics

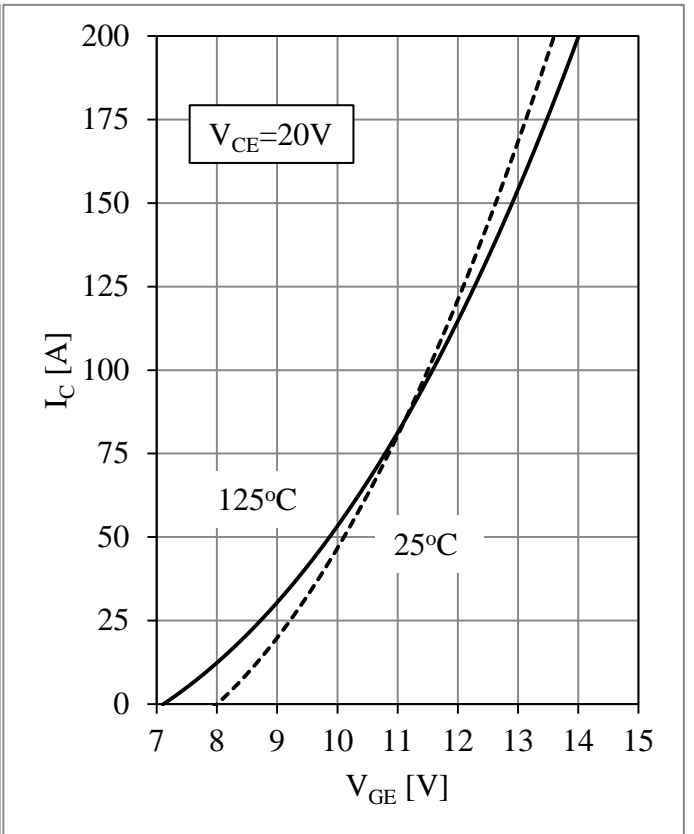


Fig 2. IGBT Transfer Characteristics

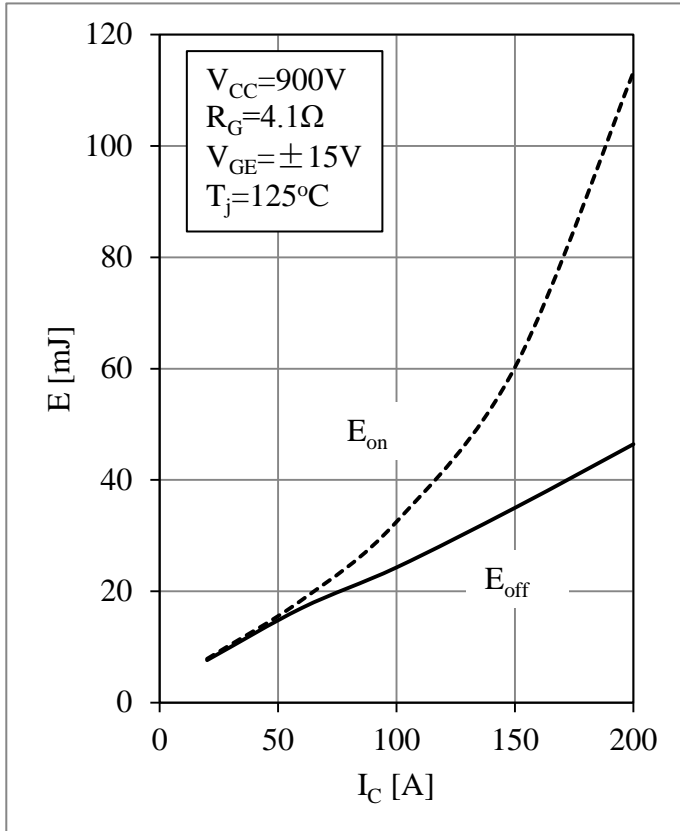


Fig 3. IGBT Switching Loss vs. I_C

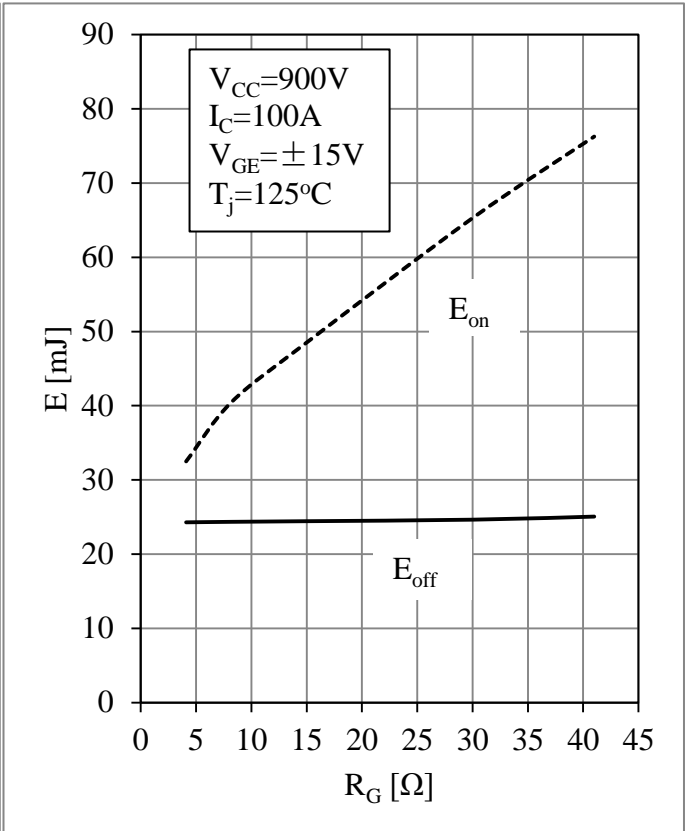


Fig 4. IGBT Switching Loss vs. R_G

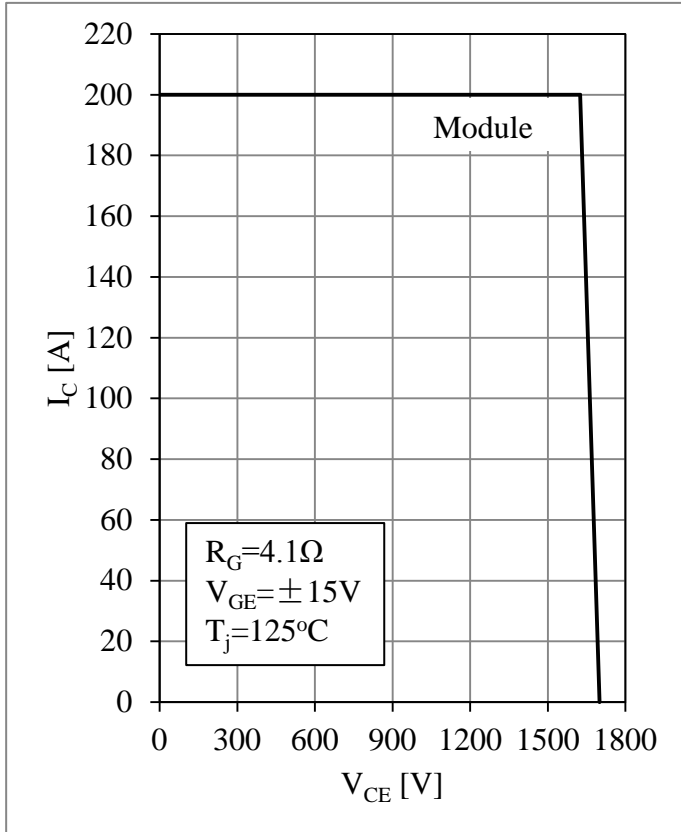


Fig 5. RBSOA

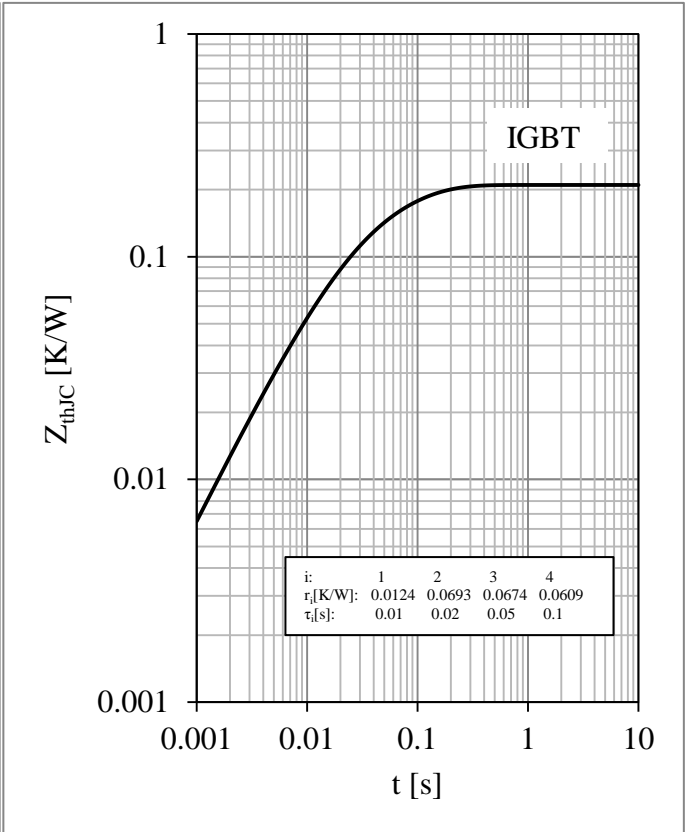


Fig 6. IGBT Transient Thermal Impedance

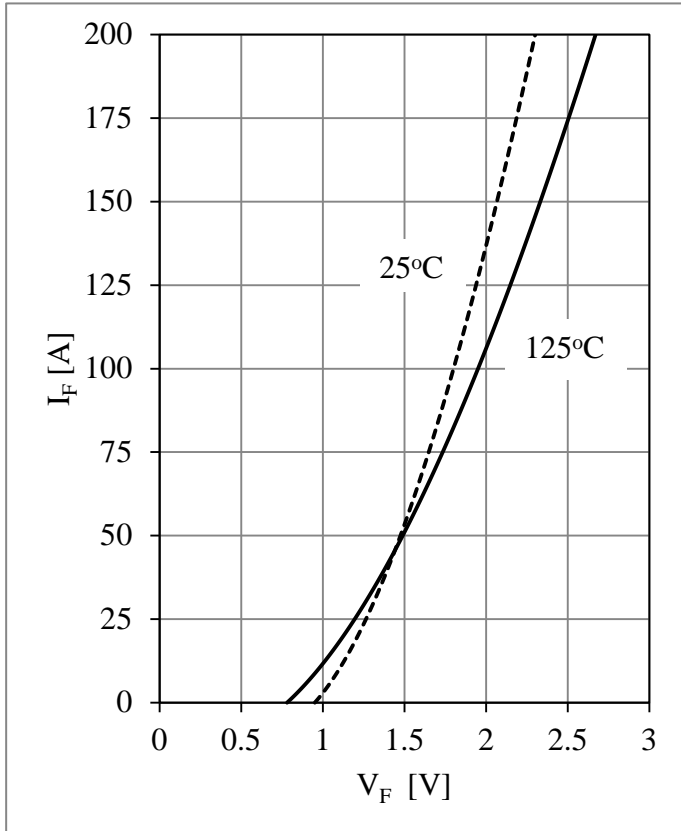


Fig 7. Diode Forward Characteristics

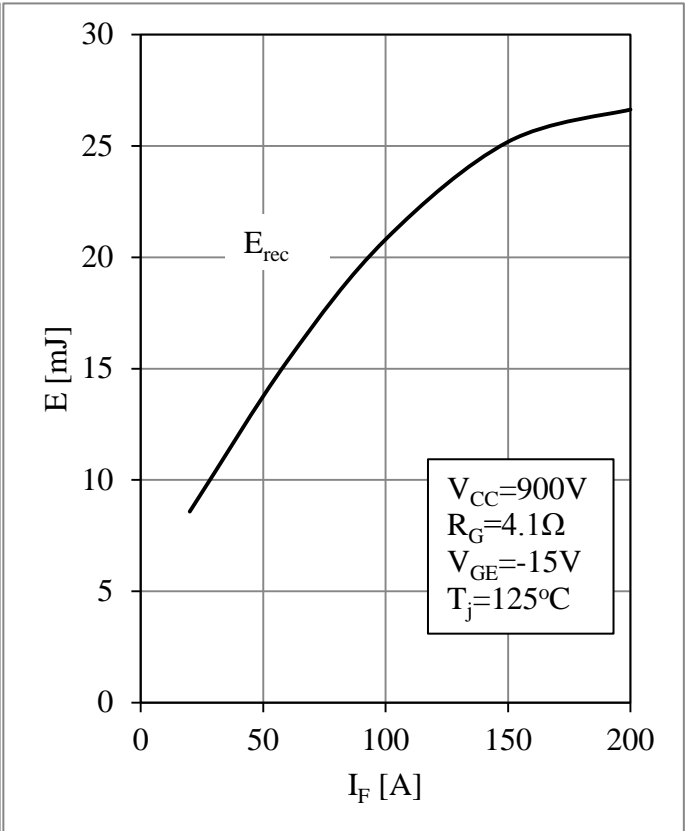


Fig 8. Diode Switching Loss vs. I_F

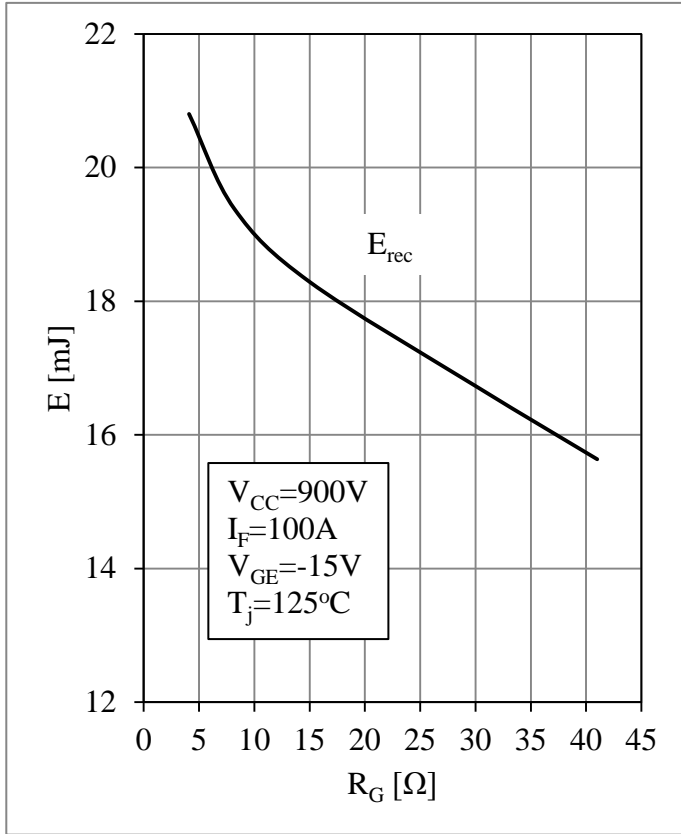


Fig 9. Diode Switching Loss vs. R_G

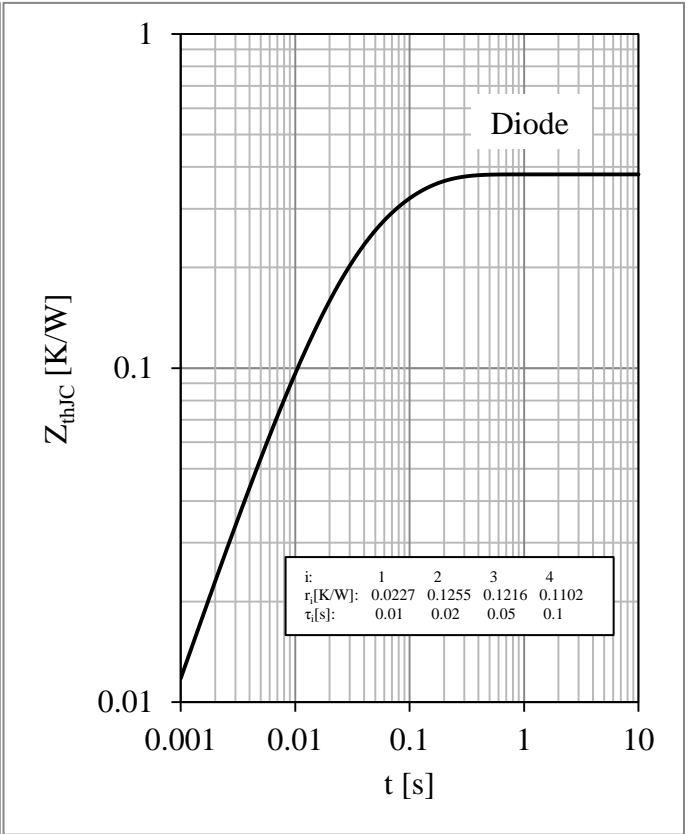


Fig 10. Diode Transient Thermal Impedance

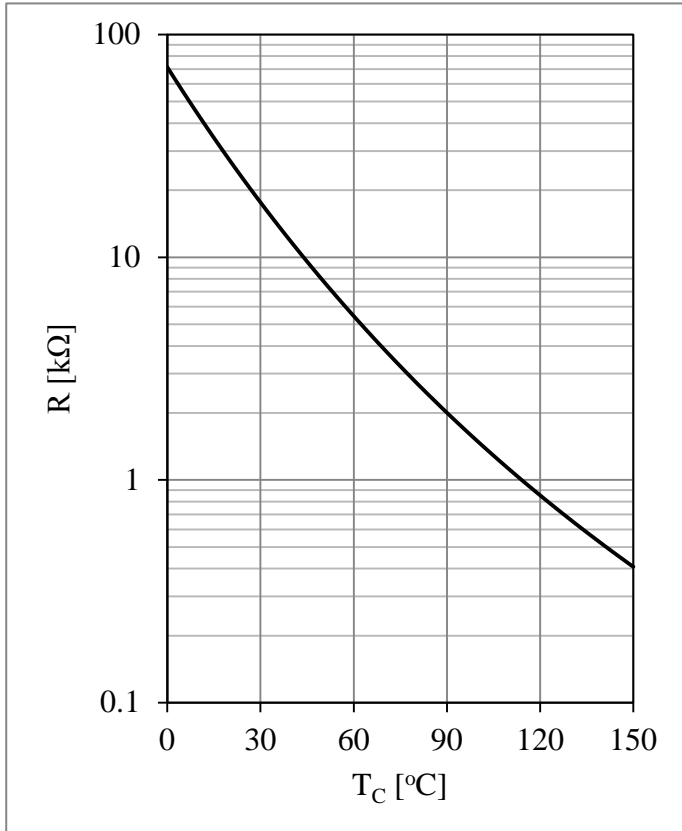
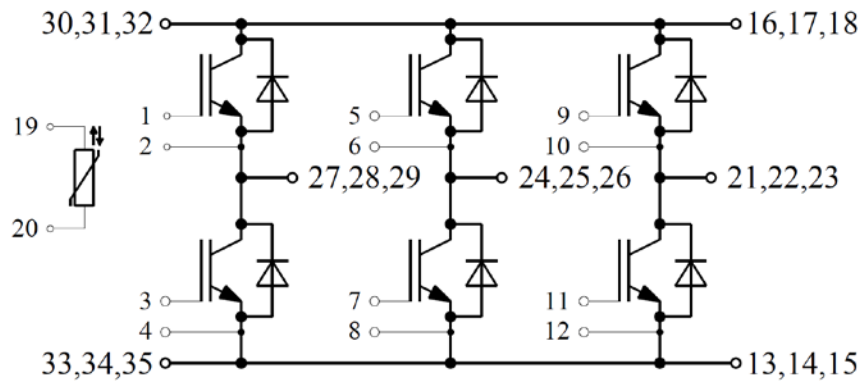


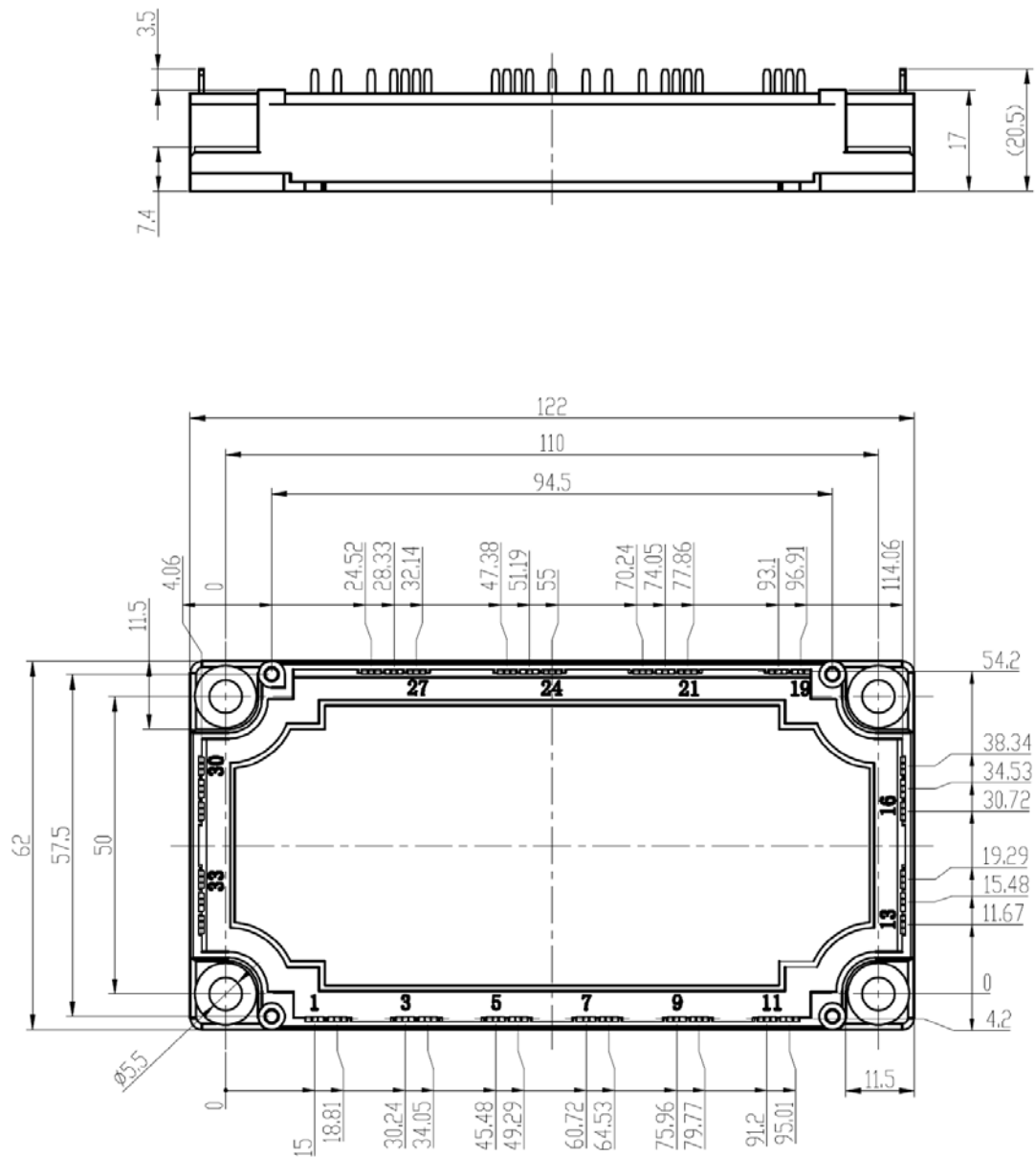
Fig 11. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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